


APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	STRUCTURE AND METHOD OF FORMING BIPOLAR TRANSISTOR HAVING A SELF-ALIGNED RAISED EXTRINSIC BASE USING SELF-ALIGNED ETCH STOP LAYER		
Application Type : regular, utility			
Attorney Docket Number : FIS920030412US1			
Correspondence address:			
Customer Number:		32074	
Inventors Information:			
<u>Inventor 1:</u>			
Applicant Authority Type:	Inventor		
Citizenship:	JO		
Given Name:	Marwan		
Middle Name:	H.		
Family Name:	Khater		
Residence:			
City of Residence:	Poughkeepsie		
State of Residence:	NY		
Country of Residence:	US		
Address-1 of Mailing Address:	606 Hudson Harbour Drive		
Address-2 of Mailing Address:			
City of Mailing Address:	Poughkeepsie		
State of Mailing Address:	NY		
Postal Code of Mailing Address:	12601		
Country of Mailing Address:	US		
Phone:			
Fax:			
E-mail:			
<u>Inventor 2:</u>			
Applicant Authority Type:	Inventor		
Citizenship:	CA		
Given Name:	Francois		

Family Name: Pagette
Residence:
City of Residence: Fishkill
State of Residence: NY
Country of Residence: US
Address-1 of Mailing Address: 1508 Max Way
Address-2 of Mailing Address:
City of Mailing Address: Fishkill
State of Mailing Address: NY
Postal Code of Mailing Address: 12524
Country of Mailing Address: US
Phone:
Fax:
E-mail:

Publication Information:
Suggested Figure for Publication - 1
Suggested Classification -
Suggested Technology Center -
Total Number of Drawing Sheets - 17

Assignee 1:

Organization Name: International Business Machines Corporation
Address-1 of Mailing Address: New Orchard Road
Address-2 of Mailing Address:
City of Mailing Address: Armonk
State of Mailing Address: NY
Postal Code of Mailing Address: 10504
Country of Mailing Address: US
Phone:
Fax:
E-mail: